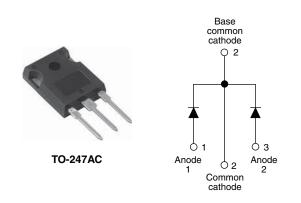
Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 2 x 8 A



PRODUCT SUMMARY							
Package	TO-247AC						
I _{F(AV)}	2 x 8 A						
V _R	600 V						
V _F at I _F	1.7 V						
t _{rr} (typ.)	18 ns						
T _J max.	150 °C						
Diode variation	Single die						

FEATURES

- · Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified for industrial level

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA16PA60CPbF is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 8 A per leg continuous current, the VS-HFA16PA60CPbF is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{BBM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16PA60CPbF is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V _R		600	V					
Maximum continuous forward currentper leg	I_	T _C = 100 °C	8						
per device	I _F	$1_{\rm C} = 100$ C	16	А					
Single pulse forward current	I _{FSM}		60	A					
Maximum repetitive forward current	I _{FRM}		24						
Maximum namer dissinction	Р	T _C = 25 °C	36	w					
Maximum power dissipation	PD	T _C = 100 °C	14	vv					
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C					

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ELECTRICAL SPECIFICATIONS PER LEG (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	600	-	-				
Maximum forward voltage		I _F = 8.0 A		-	1.4	1.7	V		
	V _{FM}	I _F = 16 A	See fig. 1	-	1.7	2.1			
		I _F = 8.0 A, T _J = 125 °C		-	1.4	1.7			
Maximum reverse	I _{RM}	V _R = V _R rated	See fig. 0	-	0.3	5.0	μA		
leakage current		$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	See fig. 2	-	100	500			
Junction capacitance C _T		V _R = 200 V	See fig. 3	-	10	25	pF		
Series inductance	L _S	Measured lead to lead 5 mm from body	-	8.0	-	nH			

DYNAMIC RECOVERY CHARACTERISTICS PER LEG (T_J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200$	0 Α/μs, V _R = 30 V	-	18	-	ns		
Reverse recovery time See fig. 5, 6 and 16	t _{rr1}	T _J = 25 °C		-	37	55			
occ lig. 5, 6 and 16	t _{rr2}	T _J = 125 °C		-	55	90			
Peak recovery current	I _{RRM1}	T _J = 25 °C	I _F = 8.0 A dI _F /dt = 200 A/μs	-	3.5	5.0	A		
See fig. 7 and 8	I _{RRM2}	T _J = 125 °C		-	4.5	8.0			
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	65	138			
See fig. 9 and 10	Q _{rr2}	T _J = 125 °C	V _R = 200 V	-	124	360	ne		
Peak rate of fall recovery current during t _h	dl _{(rec)M} /dt1	T _J = 25 °C		-	240	-	A/µs		
See fig. 11 and 12	dl _{(rec)M} /dt2	T _J = 125 °C		-	210	-	Ανμs		

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER SYMBOL		TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C				
Junction to case, single leg conducting			-	-	3.5					
Junction to case, both leg conducting	R _{thJC}		-	-	1.75	K/W				
Thermal resistance, junction to ambient		Typical socket mount	-	-	40	r./ vv				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.25	-					
Waight			-	6.0	-	g				
Weight			-	0.21	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-247AC (JEDEC)	HFA16PA60C							

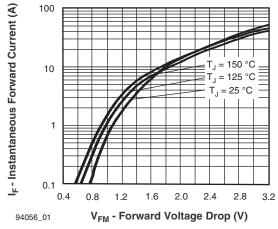
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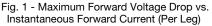
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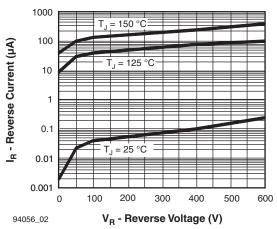


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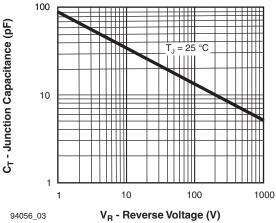
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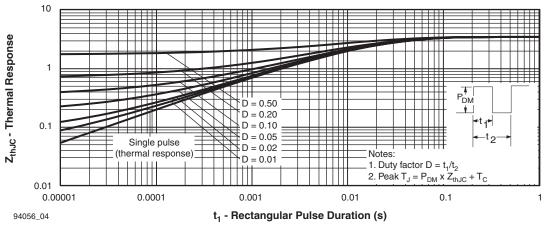














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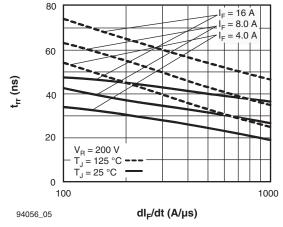


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

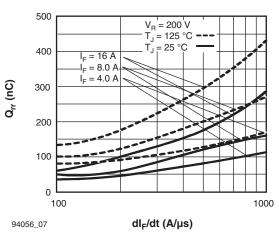


Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)

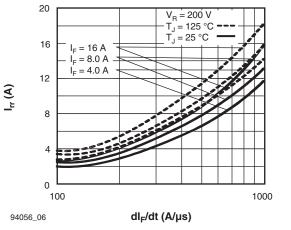


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)

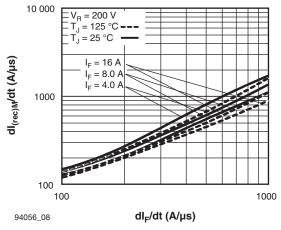


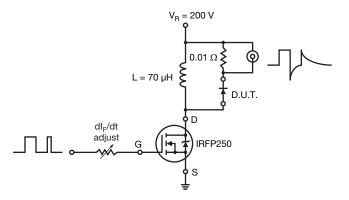
Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt (Per Leg)

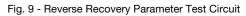
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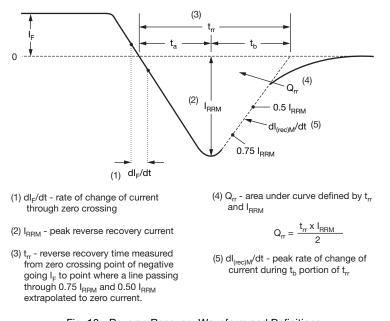


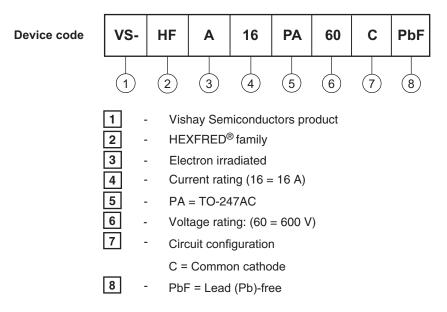
Fig. 10 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE



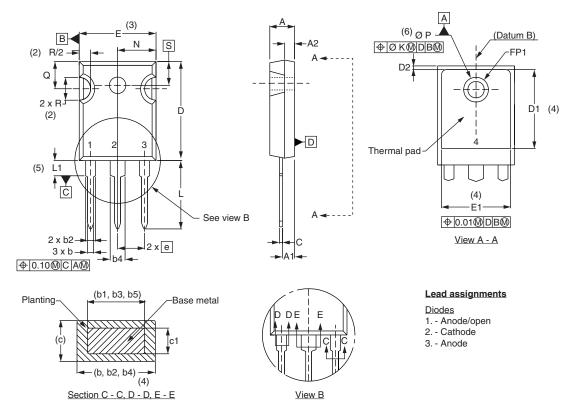
LINKS TO RELATED DOCUMENTS								
Dimensions	www.vishay.com/doc?95223							
Part marking information	www.vishay.com/doc?95226							

Outline Dimensions





DIMENSIONS in millimeters and inches



SYMBOL	DL MILLIMETERS INCHES NOTES		SYMBOL	MILLIN	IETERS	INC	HES	NOTES				
STNIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTED	STWDOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209			D2	0.51	1.30	0.020	0.051	
A1	2.21	2.59	0.087	0.102			E	15.29	15.87	0.602	0.625	3
A2	1.50	2.49	0.059	0.098			E1	13.72	-	0.540	-	
b	0.99	1.40	0.039	0.055			е	5.46	BSC	0.215	BSC	
b1	0.99	1.35	0.039	0.053			FK	2.	54	0.0)10	
b2	1.65	2.39	0.065	0.094			L	14.20	16.10	0.559	0.634	
b3	1.65	2.37	0.065	0.094			L1	3.71	4.29	0.146	0.169	
b4	2.59	3.43	0.102	0.135			N	7.62	BSC	0	.3	
b5	2.59	3.38	0.102	0.133			ΦΡ	3.56	3.66	0.14	0.144	
с	0.38	0.86	0.015	0.034			Φ P1	-	6.98	-	0.275	
c1	0.38	0.76	0.015	0.030			Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3]	R	4.52	5.49	1.78	0.216	
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	BSC	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁴⁾ Thermal pad contour optional with dimensions D1 and E1

⁽⁵⁾ Lead finish uncontrolled in L1

(6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

⁽⁷⁾ Outline conforms to JEDEC outline TO-247 with exception of dimension c

Revision: 16-Jun-11

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